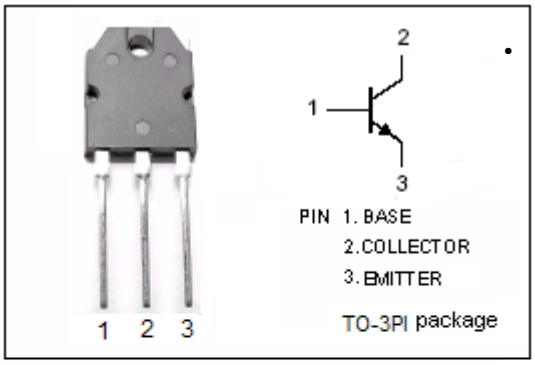
isc Silicon NPN Power Transistor 2SC3376

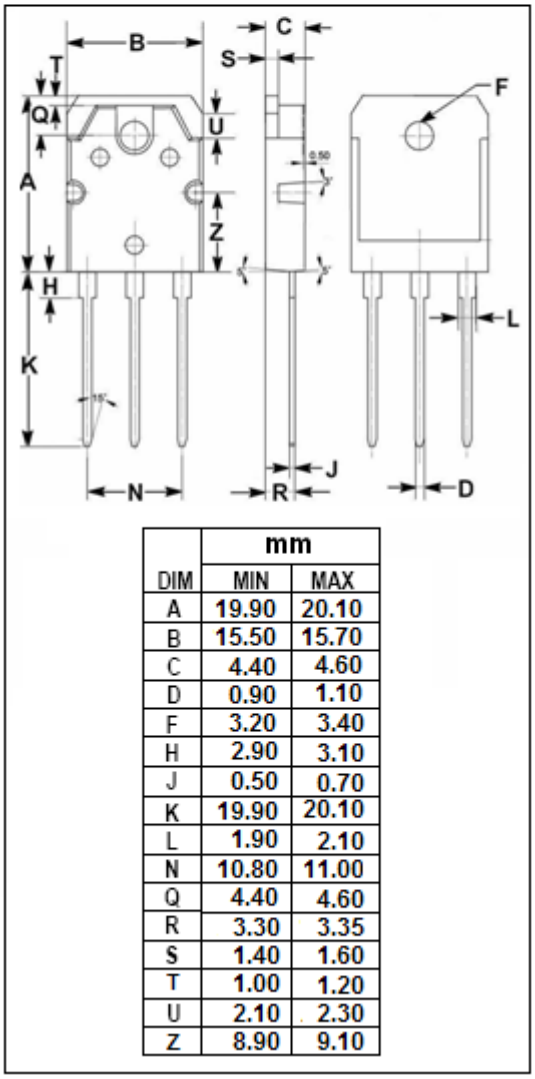


DESCRIPTION

- Collector-Emiiter Breakdown Voltage-
  : $V_{(BR)CEO}$= 800V(Min.)
- High Speed Switching

APPLICATIONS

- Switching regulator and high voltage switching applications.
- High speed DC-DC converter applications.



DIM	mm MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	900	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	3	A
I_{CM}	Collector Current-Peak	5	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @T_C=25℃	60	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

isc Silicon NPN Power Transistor 2SC3376

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	900			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.8A; I_B= 0.16A			0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 0.8A; I_B= 0.16A			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 800V; I_E= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C= 0			1.0	mA
h_{FE}	DC Current Gain	I_C= 0.8A; V_{CE}= 5V	10			
Switching Times; Resistive Load						
t_r	Rise Time	I_{B1}= 0.08A; I_{B2}= -0.2A; $V_{CC}\approx$ 400V; R_L= 500Ω			1.0	μs
t_s	Storage Time				4.0	μs
t_f	Fall Time				1.0	μs